

# THS4535 High-Precision, 60MHz, Fully Differential Amplifier

## 1 Features

- Bandwidth: 65MHz ( $G = 1V/V$ )
- Gain bandwidth product: 80MHz
- THS453x Device Comparison:
  - THS4535 offset voltage: 2mV (max)
  - THS4535 offset drift:  $1.4\mu V/^\circ C$  (max)
  - THS4536 offset voltage:  $20\mu V$  (max)
  - THS4536 offset drift:  $0.8\mu V/^\circ C$  (max)
- Supply operating range: 2.7V to 5.5V
- Low harmonic distortion:
  - HD2: 125dBc at  $2V_{PP}$ , 10kHz
  - HD3: 114dBc at  $2V_{PP}$ , 10kHz
- Slew rate:  $47V/\mu s$  &  $57V/\mu s$  (Rising & Falling)
- Low noise:
  - Voltage Noise:  $4.3nV/\sqrt{Hz}$  (2.5kHz 1/f corner)
  - Current Noise:  $70fA/\sqrt{Hz}$
- Low Bias & Offset Current:  $\pm 40pA$  at  $125^\circ C$  (max)
- Supply current: 4.7mA
- Negative rail input (NRI)
- Rail-to-rail output (RRO):
  - THS4535: 100mV from rails (typical)
  - THS4536: 80mV from rails (max)
- Temperature range:  $-40^\circ C$  to  $+125^\circ C$

## 2 Applications

- 16-bit to 20-bit, differential, SAR and  $\Delta\Sigma$  drivers
- Differential active filters
- Motor drives
- Battery testers
- Power analyzers

## 3 Description

The THS4535 is a 60MHz fully differential amplifier (FDA) that is specifically designed to drive fully differential analog-to-digital converters (ADCs) up to 2MSPS. The THS453x family offers two options: THS4535 (untrimmed) & THS4536 (trimmed).

The THS4535 is an excellent choice for simple single-to-dual conversions. FDAs such as the THS4535 offer performance benefits over traditional dual op amps, including bandwidth and phase balance between outputs and a  $VOCM$  pin to easily adjust the output common-mode voltage. For higher dc precision applications, such as high-speed low-side current shunt measurements, the THS4536 provides package level trim for offset and offset drift. THS453x devices also provide higher transient current output drive to meet the needs of successive approximation register (SAR) ADC charge injection and delta-sigma ( $\Delta\Sigma$ ) ADC precharge buffers.

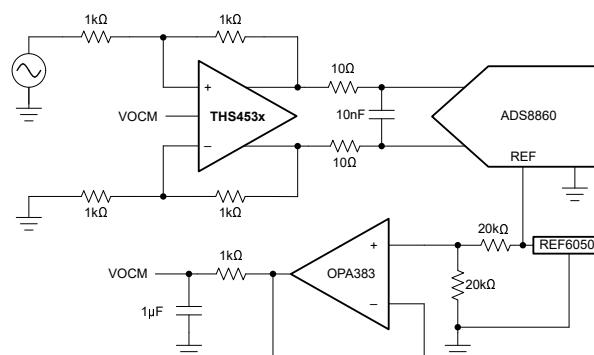
### Package Information

PART NUMBER <sup>(1)</sup>	PACKAGE <sup>(2)</sup>	PACKAGE SIZE <sup>(3)</sup>
THS4535	DGK (VSSOP, 8)	3mm x 4.9mm
	RUN (WQFN, 10)	2mm x 2mm

(1) See also [Section 4](#).

(2) For more information, see [Section 11](#).

(3) The package size (length x width) is a nominal value and includes pins, where applicable.



**Simplified Schematic: Gain of 1V/V, Single-Ended-Input to Differential-Output Interface to SAR ADC**



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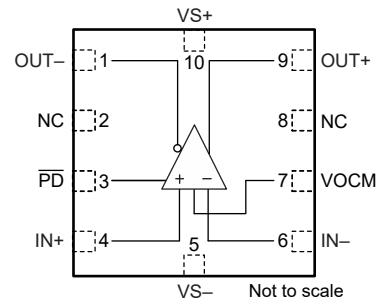
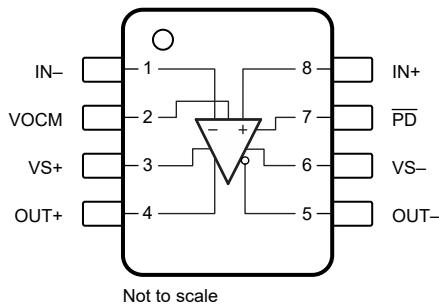
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## 4 Device Comparison Table

DEVICE	OFFSET VOLTAGE (MAX)	OFFSET DRIFT (MAX)
THS4535DGKR	2mV	1.4µV/°C
THS4536DGKR	50µV	0.8µV/°C
THS4535RUNR	2mV	1.4µV/°C
THS4536RUNR	50µV	0.8µV/°C

## 5 Pin Configuration and Functions



**Figure 5-1. DGK Package, 8-Pin VSSOP (Top View), Figure 5-2. RUN Package, 10-Pin WQFN (Top View), External Gain**

### Pin Functions

NAME	PIN		TYPE	DESCRIPTION		
	NO.					
	DGK (VSSOP)	RUN (WQFN)				
IN-	1	6	Input	Inverting (negative) amplifier input		
IN+	8	4	Input	Noninverting (positive) amplifier input		
NC	—	2, 8	—	Leave unconnected (external gain)		
OUT-	5	1	Output	Inverting (negative) amplifier output		
OUT+	4	9	Output	Noninverting (positive) amplifier output		
PD	7	3	Input	Power down. $\overline{PD}$ = logic low = power off mode; $\overline{PD}$ = logic high = normal operation.		
VOCM	2	7	Input	Output common-mode voltage control input		
VS-	6	5	Power	Negative power-supply input		
VS+	3	10	Power	Positive power-supply input		

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
$V_S$	Total supply voltage, $V_S = (V_{S+} - V_{S-})$		6	V
	Input, output, power down and common-mode pin voltage	$(V_{S-}) - 0.5$	$(V_{S+}) + 0.5$	V
$I_{IN}$	Continuous input current		$\pm 10$	mA
$I_{OUT}$	Continuous output current <sup>(2)</sup>		$\pm 65$	mA
$T_J$	Junction temperature		150	°C
$T_A$	Free-air temperature	-40	125	°C
$T_{stg}$	Storage temperature	-65	150	°C

(1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. *Absolute Maximum Ratings* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If used outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

(2) Long-term continuous output current for electromigration limits.

### 6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	$\pm 2500$	V
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002, all pins <sup>(2)</sup>	$\pm 1000$	

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
$V_S$	Total supply voltage	2.7	5.5		V
$T_J$	Junction temperature	-40	25	125	°C

## 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		THS4535		UNIT
		DGK (VSSOP)	RUN (WQFN)	
		8 PINS	10 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	151.8	147.1	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	46.4	86.9	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	86.1	85.2	°C/W
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	1.4	8.2	°C/W
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	84.7	84.9	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 6.5 Electrical Characteristics

at  $T_A = 25^\circ\text{C}$ ,  $V_{S+} - V_{S-} = 5\text{V}$ ,  $V_{OCM}$ <sup>(1)</sup> = open,  $R_F = 1\text{k}\Omega$ , differential gain ( $G$ ) =  $1\text{V/V}$ ,  $V_O = 2\text{V}_{\text{PP}}$ ,  $R_L = 1\text{k}\Omega$ , and  $\overline{PD}$  = logic high (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
<b>AC PERFORMANCE</b>							
SSBW	Small-signal bandwidth	$V_O = 100\text{mV}_{\text{PP}}$	$G = 1\text{V/V}$ , $< 1\text{dB}$ peaking	65			MHz
			$G = 2\text{V/V}$	42			
			$G = 5\text{V/V}$	16			
			$G = 10\text{V/V}$	9			
GBWP	Gain-bandwidth product	$V_O = 100\text{mV}_{\text{PP}}$ , $G = 20\text{V/V}$		80			MHz
LSBW	Large-signal bandwidth	$V_O = 2\text{V}_{\text{PP}}$ , $G = 1\text{V/V}$		17			MHz
	Bandwidth for 0.1dB flatness	$V_O = 2\text{V}_{\text{PP}}$ , $G = 1\text{V/V}$		8			MHz
SR	Slew rate (20%–80%)	$V_O = 2\text{V}$ step	Rising	47			V/ $\mu\text{s}$
			Falling	57			
	Overshoot and undershoot	$V_O = 2\text{V}$ step, 8ns input rise time		5			%
$t_S$	Settling time	$V_O = 2\text{V}$ step	To 0.1%	100			ns
			To 0.01%	150			
	Rise and fall time (10%–90%)	$V_O = 2\text{V}$ step, 8ns input rise time		30			ns
HD2	Second-order harmonic distortion	$V_O = 2\text{V}_{\text{PP}}$	$f = 1\text{kHz}$	140			dBc
			$f = 10\text{kHz}$	125			
			$f = 1\text{MHz}$	85			
		$V_O = 8\text{V}_{\text{PP}}$	$f = 1\text{kHz}$	135			
			$f = 10\text{kHz}$	125			
			$f = 1\text{MHz}$	60			
HD3	Third-order harmonic distortion	$V_O = 2\text{V}_{\text{PP}}$	$f = 1\text{kHz}$	135			dBc
			$f = 10\text{kHz}$	114			
			$f = 1\text{MHz}$	74			
		$V_O = 8\text{V}_{\text{PP}}$	$f = 1\text{kHz}$	126			
			$f = 10\text{kHz}$	106			
			$f = 1\text{MHz}$	58			
$e_n$	Input differential voltage noise	$f = 100\text{kHz}$		4.3			nV/ $\sqrt{\text{Hz}}$
		1/f corner		2.4			kHz
$i_n$	Input current noise	$f = 100\text{kHz}$		70			fA/ $\sqrt{\text{Hz}}$
	Overdrive recovery time	$G = 2\text{V/V}$		750			ns
$Z_{\text{OUT}}$	Closed-loop output impedance	$f = 100\text{kHz}$ (differential)		0.3			$\Omega$

## 6.5 Electrical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_{S+} - V_{S-} = 5\text{V}$ ,  $V_{OCM}$  (1) = open,  $R_F = 1\text{k}\Omega$ , differential gain ( $G$ ) =  $1\text{V/V}$ ,  $V_O = 2V_{PP}$ ,  $R_L = 1\text{k}\Omega$ , and  $\overline{PD}$  = logic high (unless otherwise noted)

PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
<b>DC PERFORMANCE</b>						
$A_{OL}$	Open-loop voltage gain	$V_O = \pm 2\text{V}$	100	126		$\text{dB}$
$A_{OL}$	Open-loop voltage gain	$V_O = \pm 2.3\text{V}$ , $R_L = 40\Omega$	100	126		$\text{dB}$
$V_{OS}$	Input offset voltage			$\pm 0.5$	$\pm 1.4$	$\text{mV}$
	Input offset voltage drift	$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		$\pm 0.3$	$\pm 1.4$	$\mu\text{V}/^\circ\text{C}$
$I_{B+}$ , $I_{B-}$	Input bias current <sup>(3)</sup>	$T_A = 25^\circ\text{C}$		$\pm 0.2$	$\pm 20$	$\text{pA}$
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		$\pm 20$	$\pm 40$	
$I_{OS}$	Input offset current <sup>(4)</sup>	$T_A = 25^\circ\text{C}$		$\pm 0.2$	$\pm 20$	$\text{pA}$
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		$\pm 0.2$	$\pm 30$	
<b>INPUT</b>						
$V_{ICML}$	Common-mode voltage input low	$T_A = 25^\circ\text{C}$		$V_{S-} - 0.3$	$V_{S-} - 0.2$	$\text{V}$
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		$V_{S-} - 0.2$	$V_{S-} - 0.1$	
$V_{ICMH}$	Common-mode voltage input high	$T_A = 25^\circ\text{C}$		$V_{S+} - 1.4$	$V_{S+} - 1.3$	$\text{V}$
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		$V_{S+} - 1.5$	$V_{S+} - 1.4$	
CMRR	Common-mode rejection ratio	$(V_{S-}) < V_{CM} < (V_{S+} - 1.5\text{V})$ , $T_A = 25^\circ\text{C}$	100	114		$\text{dB}$
	Differential input impedance			$15 \parallel 3.4$		$\text{T}\Omega \parallel \text{pF}$
	Common mode input impedance			$30 \parallel 1.2$		$\text{T}\Omega \parallel \text{pF}$
<b>OUTPUT</b>						
	Output voltage low	$T_A = 25^\circ\text{C}$		$V_{S-} + 0.1$	$V_{S-} + 0.2$	$\text{V}$
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		$V_{S-} + 0.1$	$V_{S-} + 0.2$	
	Output voltage high	$T_A = 25^\circ\text{C}$		$V_{S+} - 0.2$	$V_{S+} - 0.1$	$\text{V}$
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		$V_{S+} - 0.2$	$V_{S+} - 0.1$	
	Continuous output current (slam)	$V_O = \pm 2.5\text{V}$ , $R_L = 40\Omega$			$\pm 90$	$\text{mA}$
		$V_O = \pm 2.5\text{V}$ , $R_L = 40\Omega$ , $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			$\pm 80$	
	Linear output current	$V_O = \pm 2.3\text{V}$ , $R_L = 40\Omega$ , $A_{OL} > 100\text{dB}$	$T_A = 25^\circ\text{C}$	$\pm 50$	$\pm 60$	$\text{mA}$
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		$\pm 60$	
<b>OUTPUT COMMON-MODE VOLTAGE (V<sub>OCM</sub>) CONTROL</b>						
$V_{OCM}$ (1) small-signal bandwidth	$V_{VOCM} = 100\text{mV}_{PP}$			43		$\text{MHz}$
$V_{OCM}$ large-signal bandwidth	$V_{VOCM} = 1\text{V}_{PP}$			16		$\text{MHz}$
$V_{OCM}$ slew rate <sup>(2)</sup> (20%–80%)	$V_{VOCM} = 1\text{V}$ step			28		$\text{V}/\mu\text{s}$
$V_{OCM}$ voltage noise	$f = 100\text{kHz}$	$V_{VOCM} = \text{midsupply}$ (driven)		18		$\text{nV}/\sqrt{\text{Hz}}$
		$V_{VOCM} = \text{open}$		36		
DC output balance	$V_{VOCM} = \text{midsupply}$ (driven), $V_O = \pm 1\text{V}$			80		$\text{dB}$
AC output balance	$V_{VOCM} = \text{midsupply}$ (driven), $V_{OCM}/V_O$ (-3dB from dc)			50000		$\text{Hz}$
Gain error	$(V_{S-} + 0.45) < V_{VOCM} < (V_{S+} - 1.2\text{V})$		0.997	1	1.003	$\text{V}/\text{V}$
VOCM input bias current			-5	0.3	5	$\mu\text{A}$
PSRR to $V_{OCM}$				82		$\text{dB}$
VOCM input impedance				250 $\parallel$ 2.8		$\text{k}\Omega \parallel \text{pF}$
$V_{OCM}$ offset voltage	VOCM pin floating		-10		10	$\text{mV}$
$V_{OCM}$ offset voltage	$V_{VOCM} = \text{midsupply}$ (driven)		-5	0.25	5	$\text{mV}$
$V_{OCM}$ offset voltage drift	VOCM pin floating, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		-10	2	10	$\mu\text{V}/^\circ\text{C}$

## 6.5 Electrical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_{S+} - V_{S-} = 5\text{V}$ ,  $V_{OCM}$  (1) = open,  $R_F = 1\text{k}\Omega$ , differential gain ( $G$ ) =  $1\text{V/V}$ ,  $V_O = 2V_{PP}$ ,  $R_L = 1\text{k}\Omega$ , and  $\overline{PD}$  = logic high (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
	$V_{OCM}$ offset voltage drift	$V_{VOCM}$ = midsupply (driven), $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		-10	3	10	$\mu\text{V}/^\circ\text{C}$	
	VOCM voltage low	< $\pm 11\text{mV}$ shift from midsupply offset, $T_A = 25^\circ\text{C}$		$V_{S+} + 0.3$ $V_{S-} + 0.45$		$V_{S-} + 0.5$	$V$	
		< $\pm 11\text{mV}$ shift from midsupply offset, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$						
	VOCM voltage high	$T_A = 25^\circ\text{C}$ , < $\pm 11\text{mV}$ shift from midsupply offset		$V_{S+} - 1.2$	$V_{S+} - 1$	$V_{S+} - 1.3$	$V$	
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$ , < $\pm 11\text{mV}$ shift from midsupply offset						
<b>POWER SUPPLY</b>								
$I_Q$	Quiescent current	$V_S = 5\text{V}$ , $\overline{PD}$ = logic high (active)	$T_A = 25^\circ\text{C}$	4.7	5.4	$\mu\text{A}$	$\text{mA}$	
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	4.7				
$I_Q$	Quiescent current	$V_S = 5\text{V}$ , $\overline{PD}$ = logic low (shutdown)	$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	20	$\mu\text{A}$	$\mu\text{A}$	$\mu\text{A}$	
PSRR	Power-supply rejection ratio	Either supply to input $V_{OS}$		90	110	dB		
<b>POWER DOWN</b>								
	Enable voltage threshold	$\overline{PD}$ = logic high (active)		$V_{S+} - 0.5$		$V$		
	Disable voltage threshold	$\overline{PD}$ = logic low (shutdown)		$V_{S-} + 0.5$		$V$		
	Enable pin bias current	$\overline{PD}$ = high		0	6	$\mu\text{A}$	$\mu\text{A}$	
		$\overline{PD}$ = low		-15				
	Turn-on time delay	Time from $\overline{PD}$ = high to $V_O$ = 90% of final value		5	$\text{us}$	$\text{us}$	$\text{us}$	
	Turn-off time delay	Time from $\overline{PD}$ = low to $V_O$ = 10% of original value		40	$\text{ns}$	$\text{ns}$	$\text{ns}$	

(1)  $V_{VOCM}$  refers to the voltage at VOCM pin.  $V_{OCM} = [(V_{OUT+} + V_{OUT-}) / 2]$  refers to the average output voltage.

(2) Average of the rising and falling slew rate.

(3) Current out of the node is considered positive.

(4)  $I_{OS} = I_{B+} - I_{B-}$ .

## 6.6 Typical Characteristics

at  $T_A = 25^\circ\text{C}$ ,  $V_{S+} - V_{S-} = 5\text{V}$ ,  $V_{O\text{CM}} = \text{open}$  (midsupply),  $R_F = 1\text{k}\Omega$ ,  $G = 1\text{V/V}$ ,  $V_O = 2\text{V}_{\text{PP}}$ ,  $R_L = 1\text{k}\Omega$ , and  $\overline{PD} = \text{logic high}$  (unless otherwise noted)

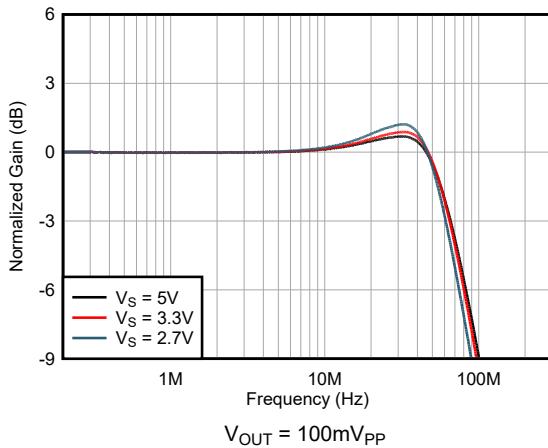


Figure 6-1. Small-Signal Bandwidth vs Supply Voltage

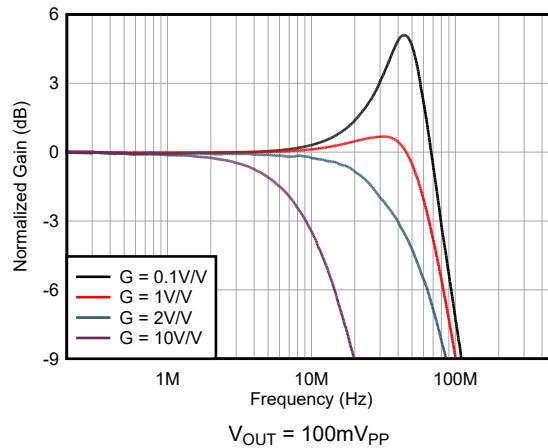


Figure 6-2. Small-Signal Bandwidth vs Gain

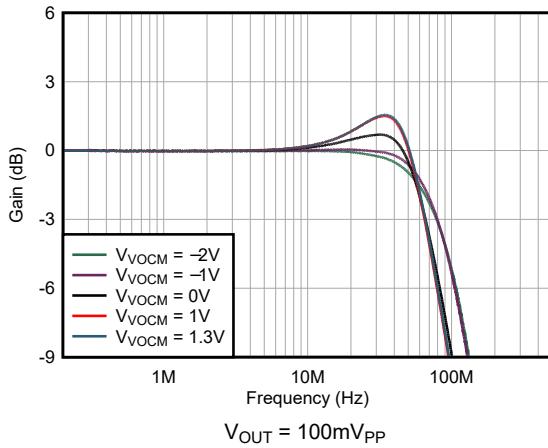


Figure 6-3. Small-Signal Bandwidth vs Output Common-Mode

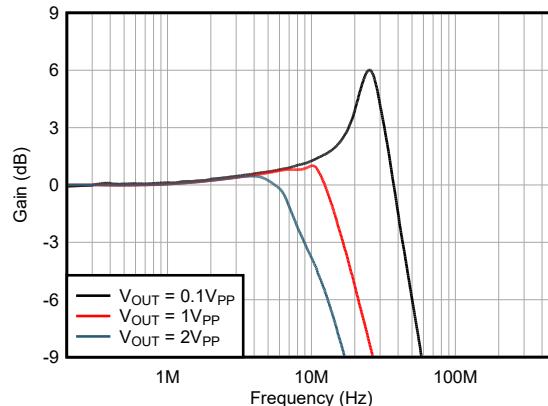


Figure 6-4.  $V_{\text{O}\text{CM}}$  Bandwidth vs  $V_{\text{O}\text{CM}}$  Amplitude

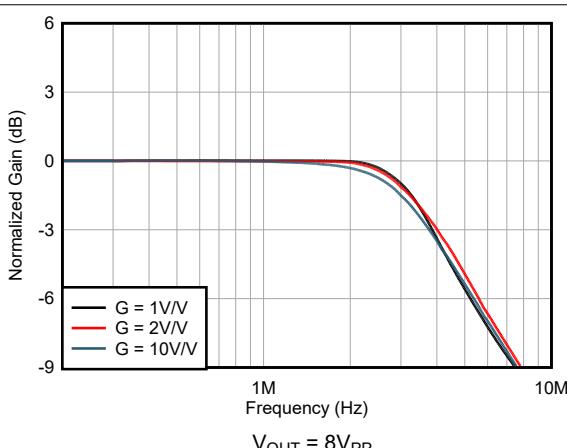


Figure 6-5. Large-Signal Bandwidth vs Gain

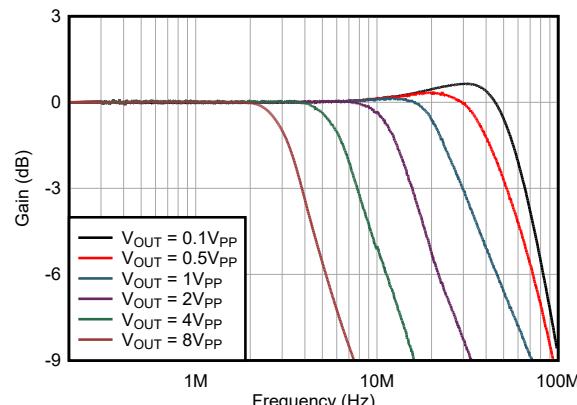


Figure 6-6. Large-Signal Bandwidth vs Output Amplitude

## 6.6 Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_{S+} - V_{S-} = 5\text{V}$ ,  $V_{OCM} = \text{open}$  (midsupply),  $R_F = 1\text{k}\Omega$ ,  $G = 1\text{V/V}$ ,  $V_O = 2\text{V}_{PP}$ ,  $R_L = 1\text{k}\Omega$ , and  $\overline{PD} = \text{logic high}$  (unless otherwise noted)

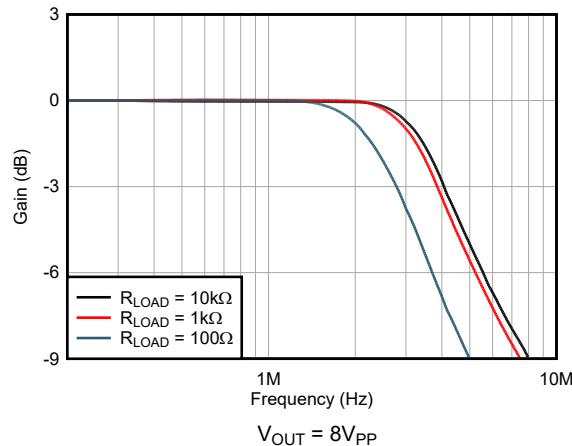


Figure 6-7. Large-Signal Bandwidth vs Load Resistance

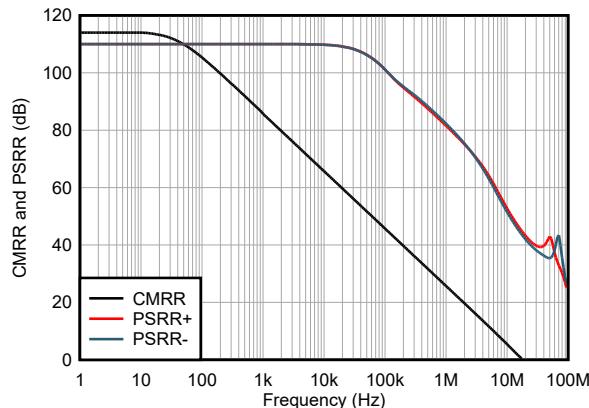


Figure 6-8. Common-Mode and Power Supply Rejection vs Frequency

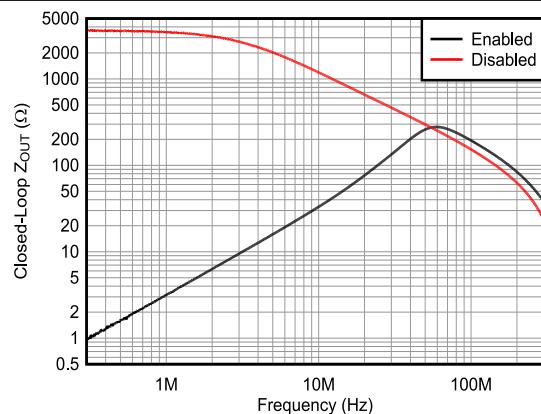


Figure 6-9. Closed Loop Output Impedance vs Frequency

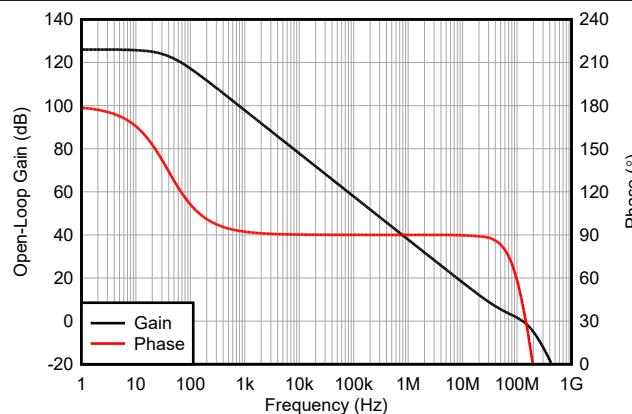


Figure 6-10. Open Loop Gain & Phase vs Frequency

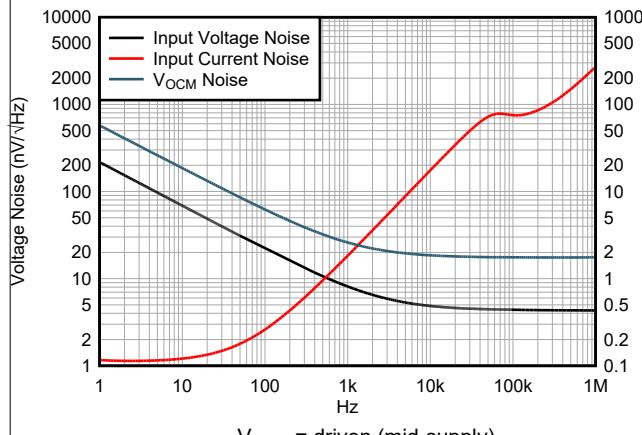


Figure 6-11. Voltage Noise vs Frequency

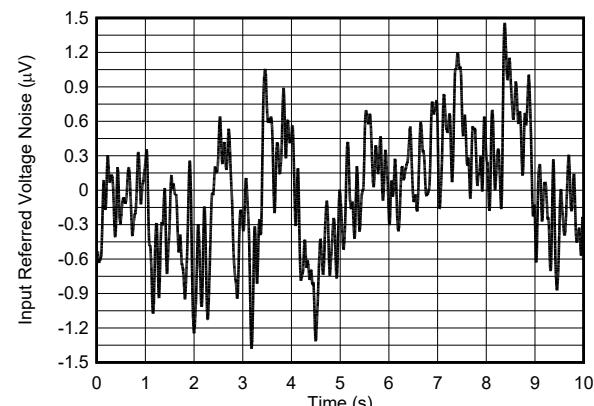


Figure 6-12. 0.1Hz to 10Hz Voltage Noise

## 6.6 Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_{S+} - V_{S-} = 5\text{V}$ ,  $V_{O\text{CM}} = \text{open}$  (midsupply),  $R_F = 1\text{k}\Omega$ ,  $G = 1\text{V/V}$ ,  $V_O = 2\text{V}_{\text{PP}}$ ,  $R_L = 1\text{k}\Omega$ , and  $\overline{PD} = \text{logic high}$  (unless otherwise noted)

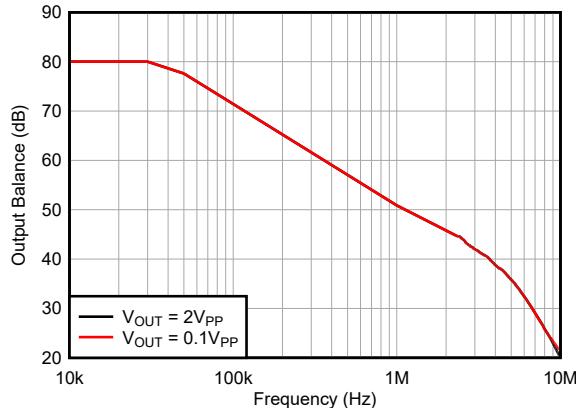


Figure 6-13. Output Balance vs Frequency

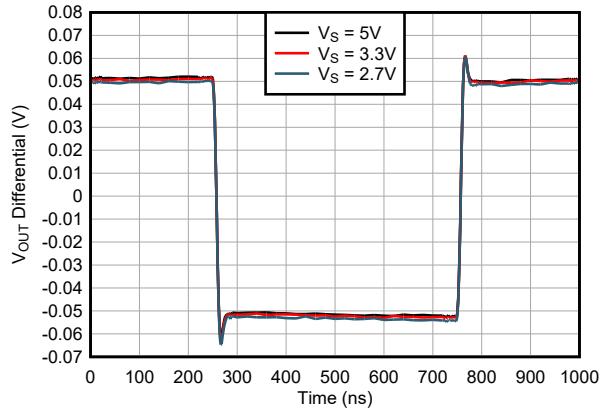


Figure 6-14. Small-Signal Step Response vs Supply Voltage

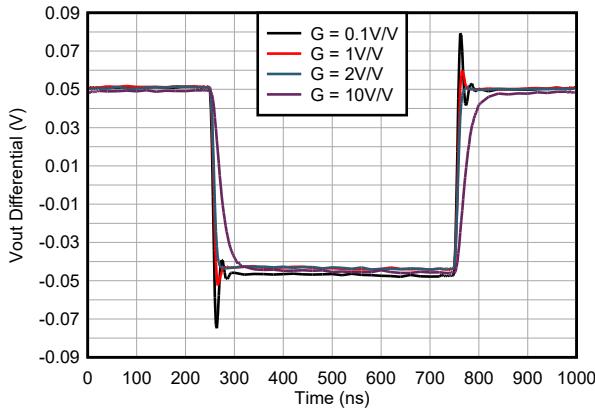


Figure 6-15. Small-Signal Step Response vs Gain

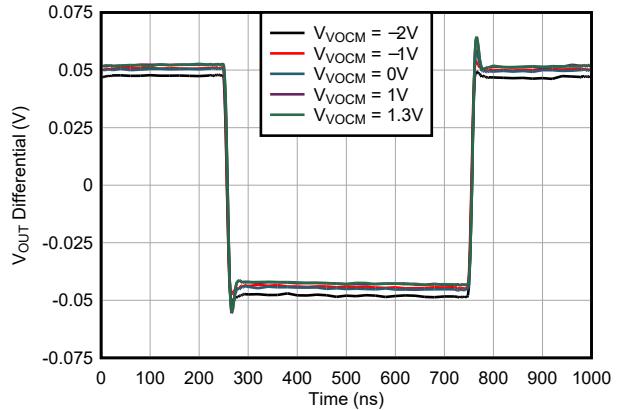


Figure 6-16. Small-Signal Step Response vs Output Common-Mode

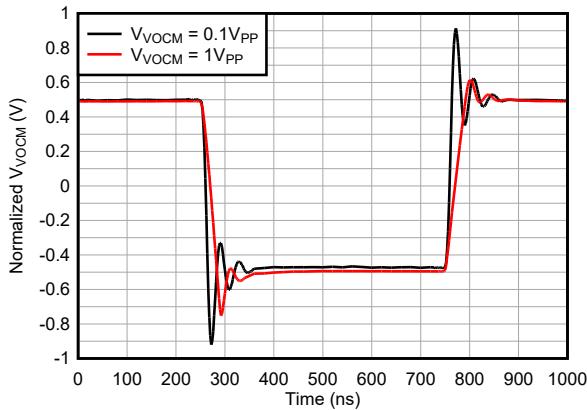


Figure 6-17. Output Common-Mode Step Response

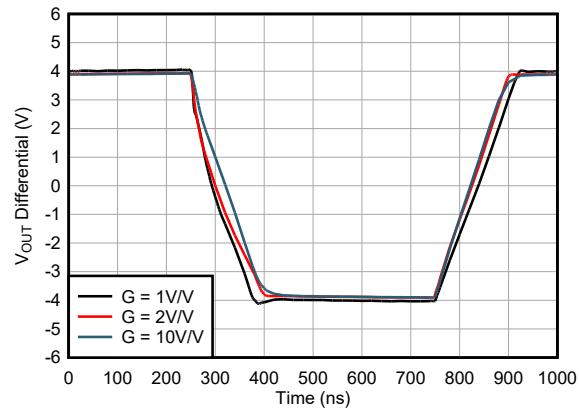


Figure 6-18. Large-Signal Step Response vs Gain

## 6.6 Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_{S+} - V_{S-} = 5\text{V}$ ,  $V_{OCM} = \text{open}$  (midsupply),  $R_F = 1\text{k}\Omega$ ,  $G = 1\text{V/V}$ ,  $V_O = 2\text{V}_{\text{PP}}$ ,  $R_L = 1\text{k}\Omega$ , and  $\overline{PD} = \text{logic high}$  (unless otherwise noted)

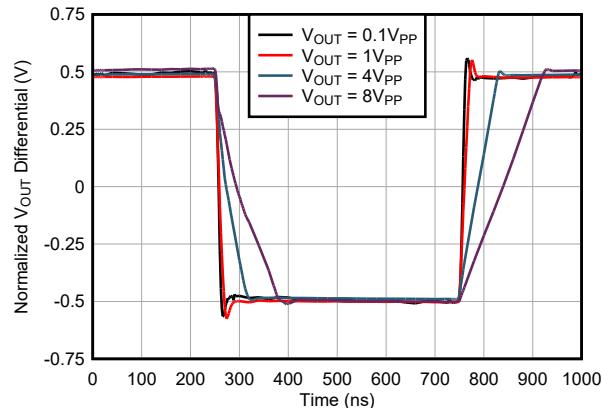


Figure 6-19. Large-Signal Step Response vs Output Amplitude

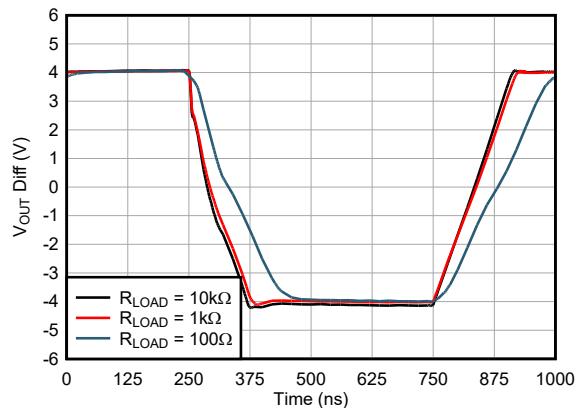


Figure 6-20. Large Signal Step Response vs Resistive Load

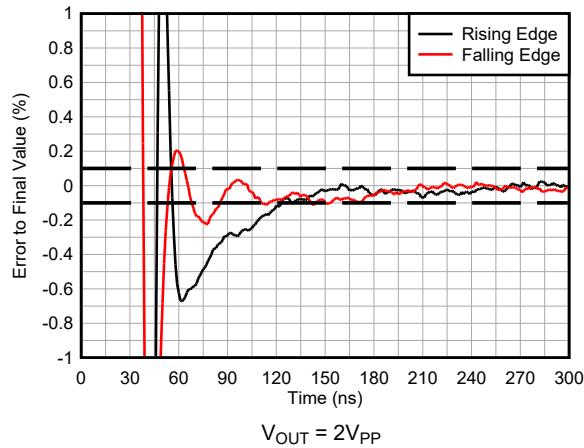


Figure 6-21. Large Signal Settling Time

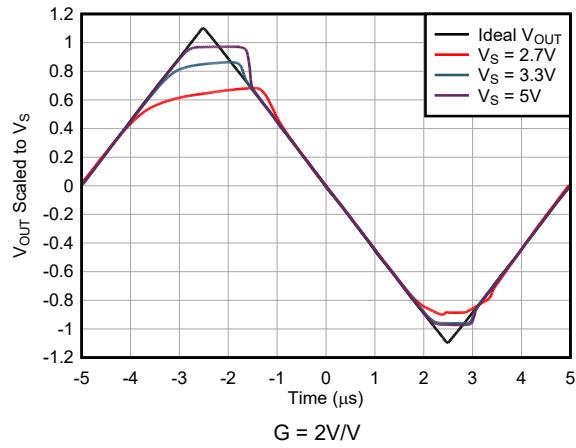


Figure 6-22. Overload Recovery Time vs Supply Voltage

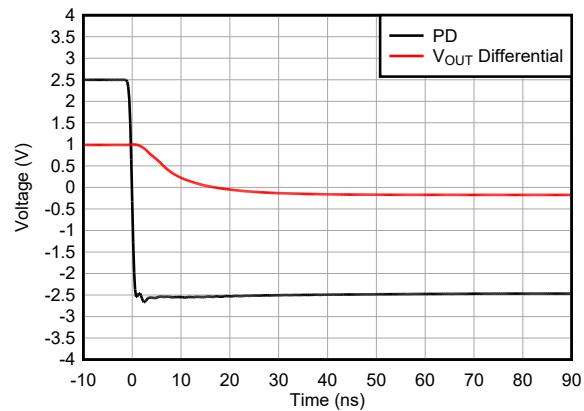


Figure 6-23. Output Disable Time

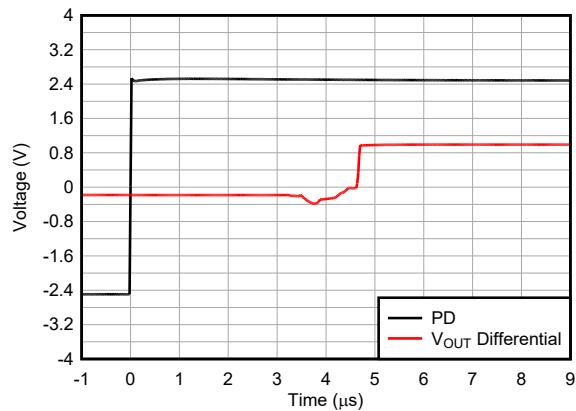


Figure 6-24. Output Enable Time

## 6.6 Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_{S+} - V_{S-} = 5\text{V}$ ,  $V_{OCM} = \text{open}$  (midsupply),  $R_F = 1\text{k}\Omega$ ,  $G = 1\text{V/V}$ ,  $V_O = 2\text{V}_{\text{PP}}$ ,  $R_L = 1\text{k}\Omega$ , and  $\overline{PD} = \text{logic high}$  (unless otherwise noted)

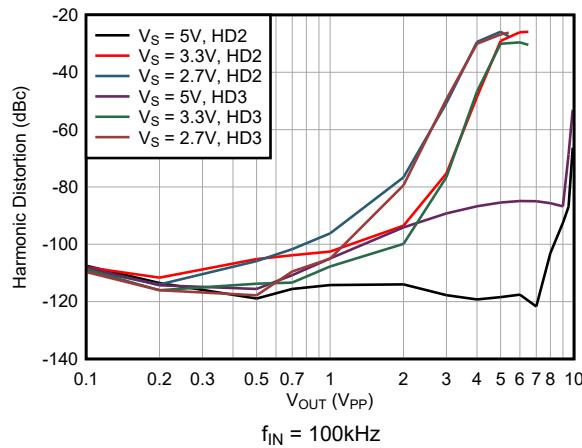


Figure 6-25. Harmonic Distortion vs Output Amplitude

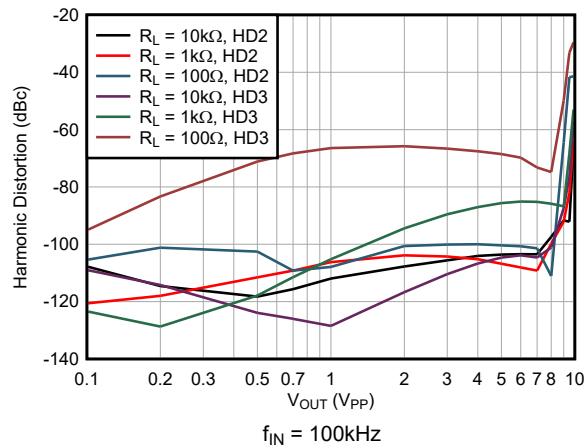


Figure 6-26. Harmonic Distortion vs Output Amplitude

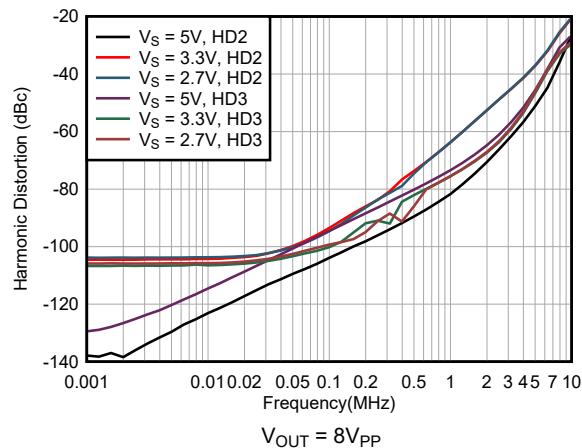


Figure 6-27. Harmonic Distortion vs Frequency

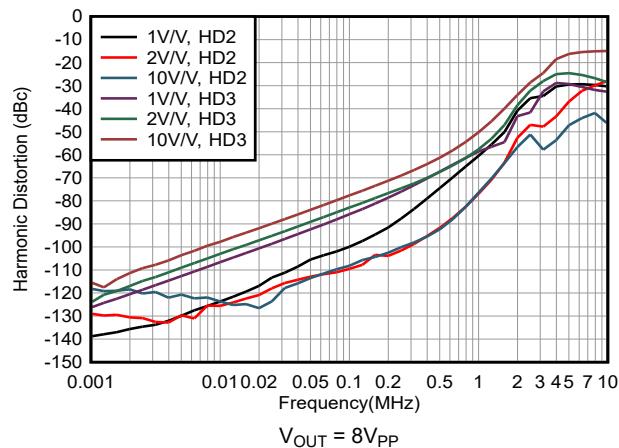


Figure 6-28. Harmonic Distortion vs Frequency

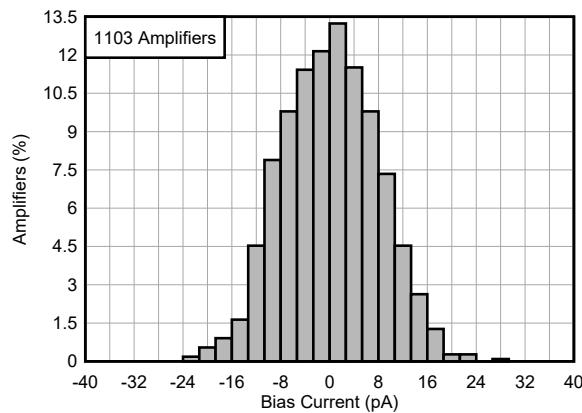


Figure 6-29. Input Bias Current Distribution

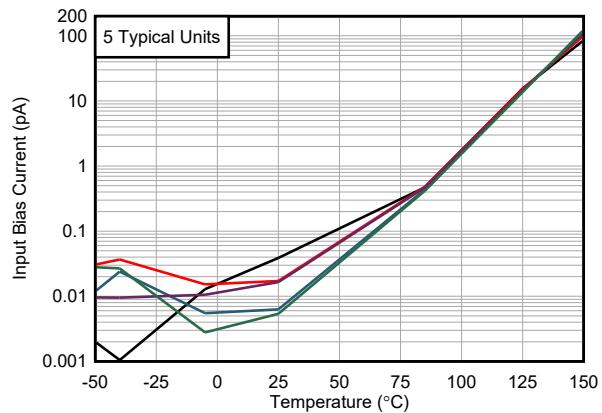


Figure 6-30. Input Bias Current vs Temperature

## 6.6 Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_{S+} - V_{S-} = 5\text{V}$ ,  $V_{OCM} = \text{open}$  (midsupply),  $R_F = 1\text{k}\Omega$ ,  $G = 1\text{V/V}$ ,  $V_O = 2\text{V}_{\text{PP}}$ ,  $R_L = 1\text{k}\Omega$ , and  $\overline{PD} = \text{logic high}$  (unless otherwise noted)

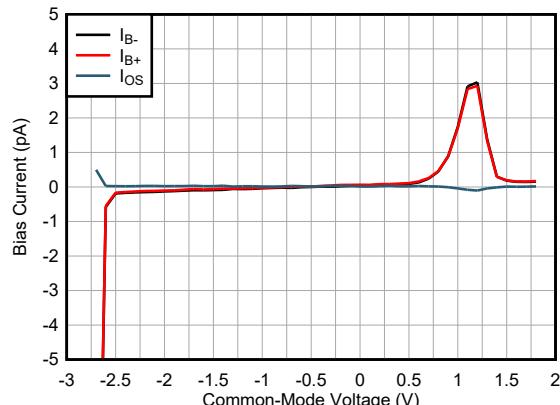


Figure 6-31. Input Bias Current vs Input Common-Mode Voltage

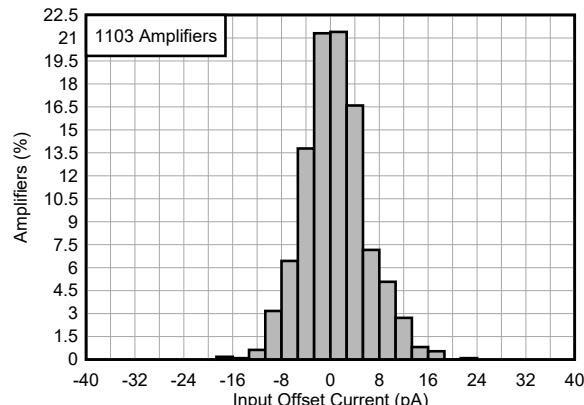


Figure 6-32. Input Offset Current Distribution

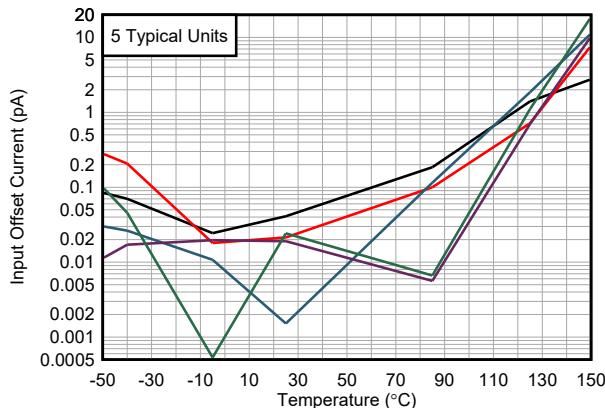


Figure 6-33. Input Offset Current vs Temperature

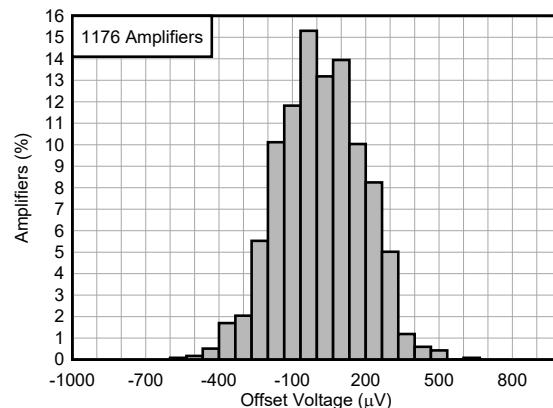


Figure 6-34. THS4535 Offset Voltage Distribution

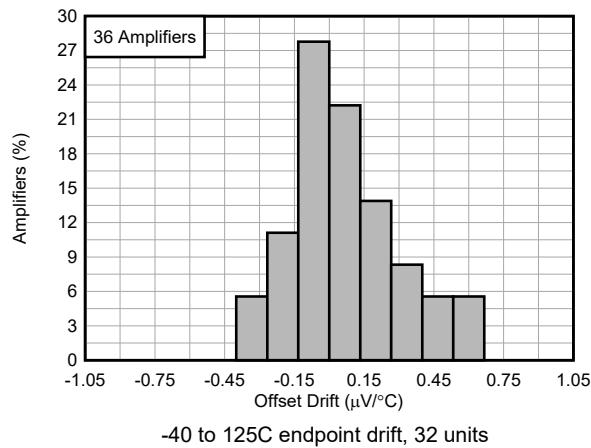


Figure 6-35. THS4535 Offset Voltage Drift Distribution

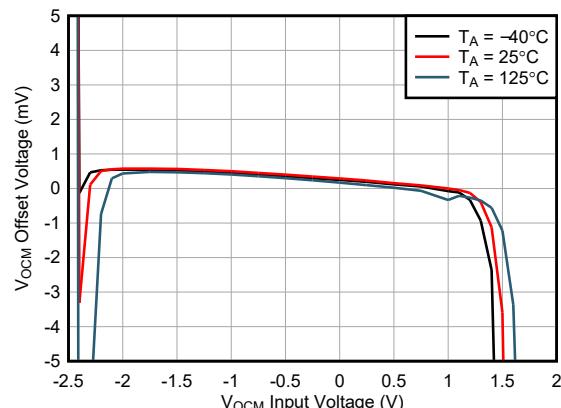


Figure 6-36. Output Common-Mode Offset Voltage vs VOCM Voltage

## 6.6 Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_{S+} - V_{S-} = 5\text{V}$ ,  $V_{OCM} = \text{open}$  (midsupply),  $R_F = 1\text{k}\Omega$ ,  $G = 1\text{V/V}$ ,  $V_O = 2V_{PP}$ ,  $R_L = 1\text{k}\Omega$ , and  $\overline{PD} = \text{logic high}$  (unless otherwise noted)

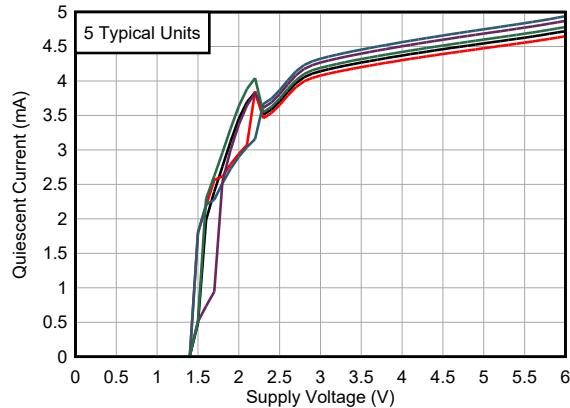


Figure 6-37. Quiescent Current vs Supply Voltage

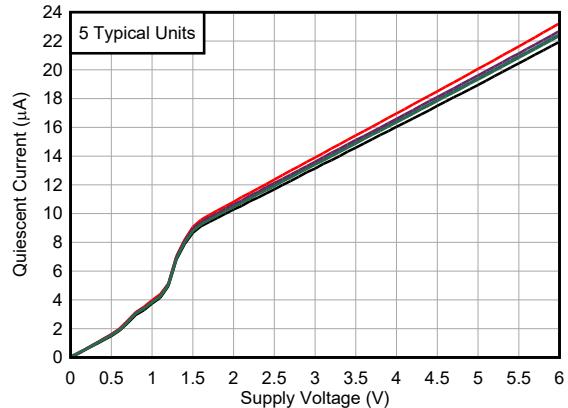


Figure 6-38. Power-Down Quiescent Current vs Supply Voltage

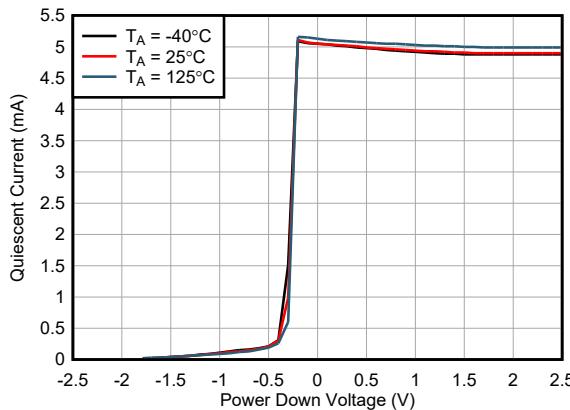


Figure 6-39. Quiescent Current vs  $\overline{PD}$  Voltage

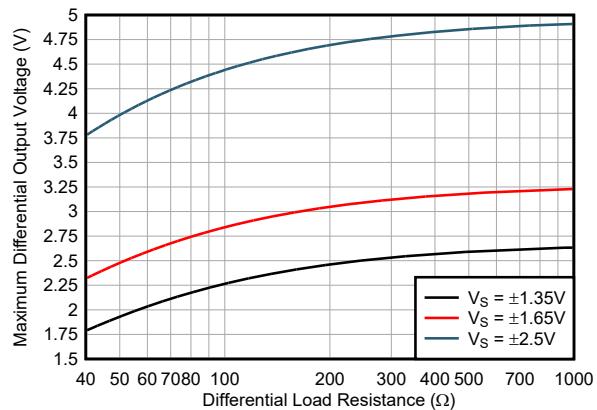


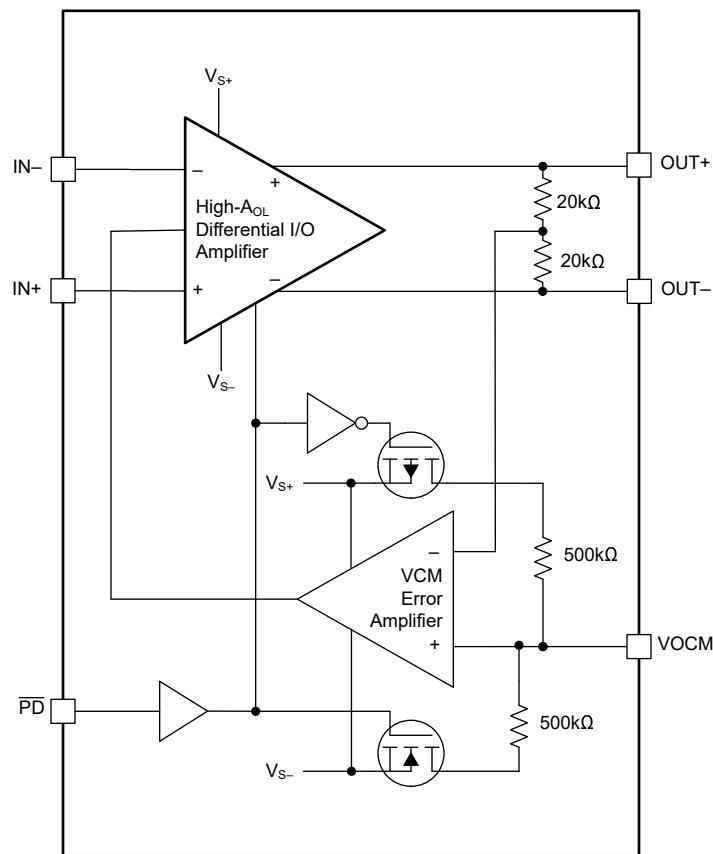
Figure 6-40. Maximum Differential Output Voltage vs Differential Load Resistance

## 7 Detailed Description

## 7.1 Overview

The THS4535 is a fully differential CMOS amplifier designed to optimize dc and ac performance for driving < 2MSPS ADCs. The base version of this device, THS4535, is designed for single-ended to differential conversions in low-side current sensing or funnel amplifier applications. When dc precision is needed, the THS4536 provides a temperature trimmed version of the device. This temperature trimming, along with state of the art package construction, allows applications in data acquisition systems (DAQ) to minimize errors due to temperature drift, long-term drift, or applications that are sensitive to overtemperature shifts in bias current or input offset current.

## 7.2 Functional Block Diagram



## 7.3 Feature Description

### 7.3.1 Output Common-Mode

The THS4535 output common-mode pin allows the FDA to servo the output pins ( $V_{OUT+}$  and  $V_{OUT-}$ ) so that the average voltage of these two pins matches the  $V_{OCM}$  pin.  $V_{OCM}$  is especially useful when the input common-mode voltage does not match the desired output common-mode voltage, such as in ADC drive. For example, in the case of a high-side current sense measurement there is often a large common-mode voltage followed by a small differential voltage. If the high-side shunt resistor common-mode voltage is close to the positive supply (Figure 7-1), set the  $V_{OCM}$  pin to  $\frac{1}{2}$  the ADC reference voltage, and the differential output voltage is gained up and balanced around the  $V_{OCM}$  voltage.

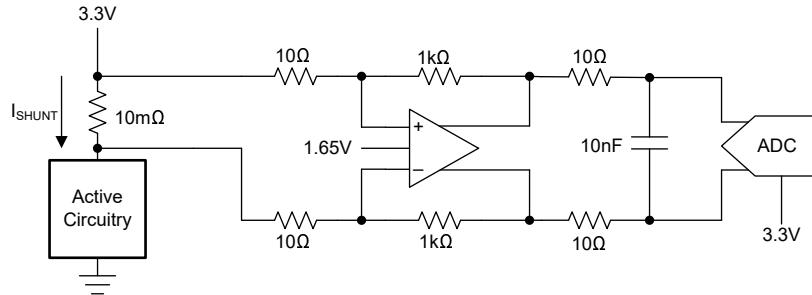


Figure 7-1. High-Side Current-Sense Example

#### Note

The THS4535  $V_{OCM}$  pin has an internal voltage divider with two  $500\text{k}\Omega$  resistors, one connected to  $V_{S+}$  and one connected to  $V_{S-}$ . If this pin is left unconnected connect a  $1\text{nF}$  capacitor from  $V_{OCM}$  to ground to help stabilize the pin voltage internally.

## 7.4 Device Functional Modes

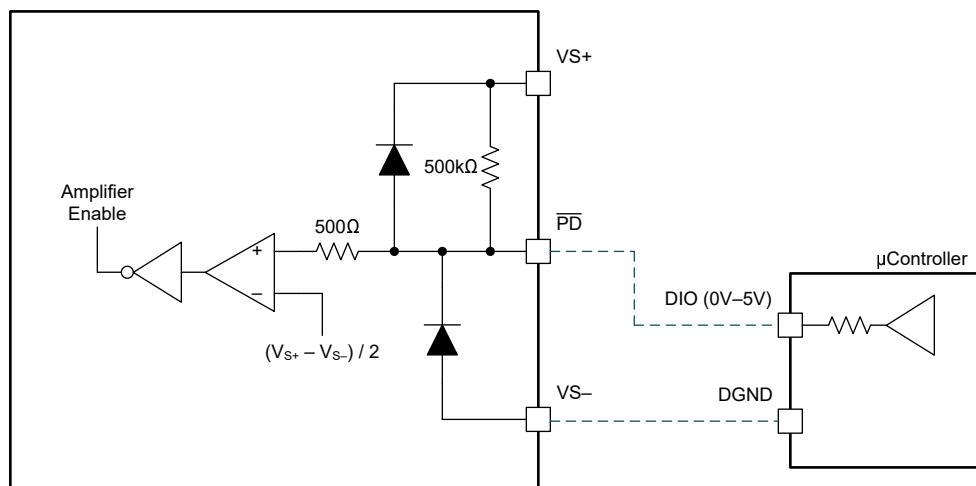
### 7.4.1 Power-Down Mode

Assert the power-down ( $\overline{PD}$ ) pin to the desired voltage for proper power-down mode operation. A physical internal pullup resistor of 500k is provided internally on the  $\overline{PD}$  pin so that if the pin is floated, the device defaults to the ON state. Tie the  $\overline{PD}$  pin to the positive supply voltage for applications that simply require the device to power on when the supplies are present. For single-supply operation, a minimum of 0.5V within the positive supply is required.

The disable operation is referenced from the negative supply. For an OFF state condition, the disable control pin must be 0.5V within the negative supply. [Figure 7-2](#) shows how to use a microcontroller to toggle the power-down pin on the THS4535 by simply connecting a digital input/output (DIO) directly to the  $\overline{PD}$  pin.

#### Note

If using a microcontroller to enable the THS4535, ensure that the threshold voltages (VIH and VIL) in the *Electrical Characteristics* are satisfied.



**Figure 7-2.  $\overline{PD}$  Pin Schematic**

## 8 Application and Implementation

### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 8.1 Application Information

Most applications for the THS4535 strive to deliver the best dynamic range in a design that delivers the desired signal processing along with adequate phase margin for the amplifier. The following sections detail some of the design issues with analysis and guidelines for improved performance.

#### 8.1.1 Output Common-Mode Voltage

The output common-mode voltage pin sets the dc output voltage of the THS4535. A voltage applied to the VOCM pin from a low-impedance source is used to directly set the output common-mode voltage. If left floating, then the VOCM pin defaults to the midrail voltage, defined as:

$$\frac{(V_{CC+}) + (V_{CC-})}{2} \quad (1)$$

To minimize common-mode noise, connect a  $0.1\mu F$  bypass capacitor to the VOCM pin. Output common-mode voltage causes additional current to flow in the feedback resistor network. This current is supplied by the output stage of the amplifier; therefore, additional power dissipation is created. For commonly-used feedback resistance values, this current is easily supplied by the amplifier. The additional internal power dissipation created by this current is potentially significant in some applications, and dictates the use of the PowerPAD integrated circuit package to effectively control self-heating.

##### 8.1.1.1 Resistor Matching

Resistor matching is important in FDAs to maintain good output balance. An ideal differential output signal implies the two outputs of the FDA are exactly equal in amplitude and shifted  $180^\circ$  in phase. Any imbalance in amplitude or phase between the two output signals results in an undesirable common-mode signal at the output. The output balance error is a measure of how well the outputs are balanced, and is defined as the ratio of the output common-mode voltage to the output differential signal.

$$\text{Output Balance Error} = \frac{\left(\frac{V_{OUT+} - V_{OUT-}}{2}\right)}{V_{OUT+} - V_{OUT-}} \quad (2)$$

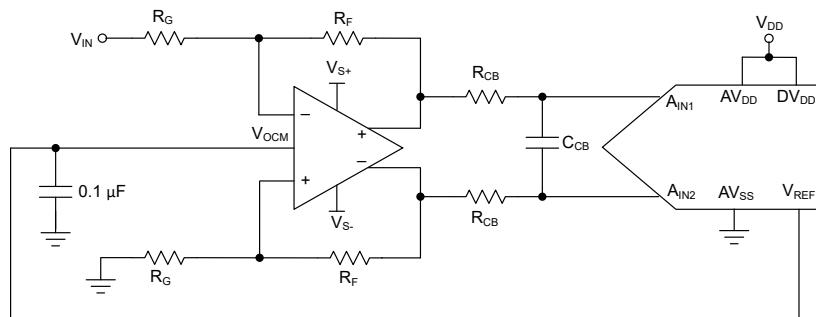
At low frequencies, resistor mismatch is the primary contributor to output balance errors. Additionally CMRR, PSRR, and HD2 performance diminish if resistor mismatch occurs. Therefore, to optimize performance, use 1% tolerance resistors or better. [Table 8-1](#) provides the recommended resistor values to use for a particular gain.

**Table 8-1. Recommended Resistor Values**

GAIN (V/V)	$R_G$ ( $\Omega$ )	$R_F$ ( $\Omega$ )
1	1000	1000
2	499	1000
5	200	1000
10	100	1000

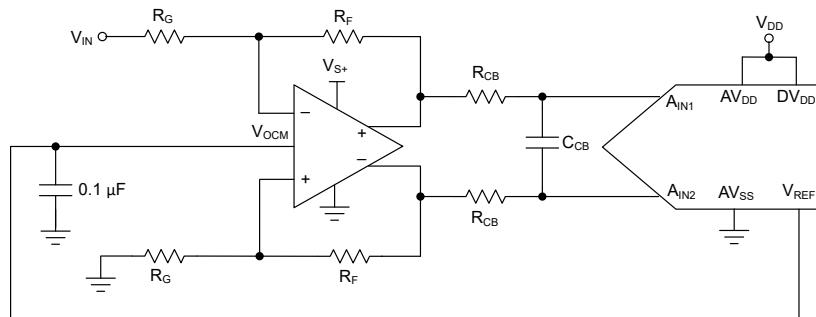
#### 8.1.2 Data Converters

Driving data converters is one of the most popular applications for fully-differential amplifiers. [Figure 8-1](#) shows a typical configuration of an FDA attached to a differential analog-to-digital converter (ADC).



**Figure 8-1. Fully-Differential Amplifier Attached to a Differential ADC**

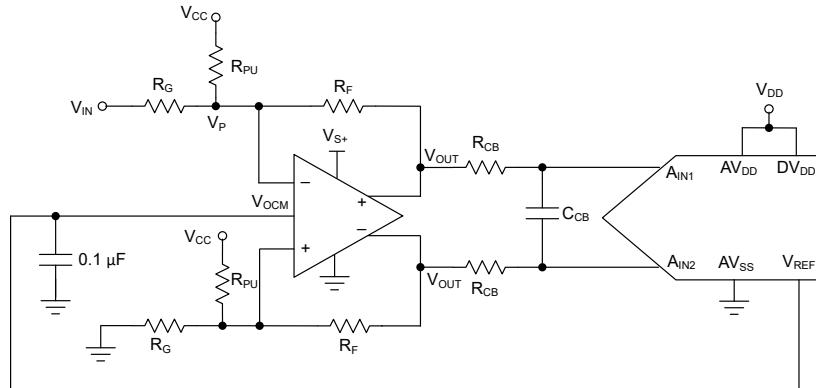
FDAs are able to operate with a single supply.  $V_{OCM}$  defaults to the midrail voltage,  $V_{CC} / 2$ . The differential output is fed into a data converter. This method eliminates the use of a transformer in the circuit. If the ADC has a reference voltage output ( $V_{REF}$ ), then connect  $V_{REF}$  directly to the  $V_{OCM}$  of the amplifier using a bypass capacitor to reduce broadband common-mode noise.



**Figure 8-2. Fully-Differential Amplifier Using a Single Supply**

### 8.1.3 Single-Supply Applications

For proper operation, do not exceed the common-mode input voltage range of the device. However, some single-supply applications require that the input voltage exceeds the common-mode input voltage range. In this case, to bring the common-mode input voltage within the specifications of the amplifier, use the circuit configuration of Figure 8-3.



**Figure 8-3. Circuit With Improved Common-Mode Input Voltage**

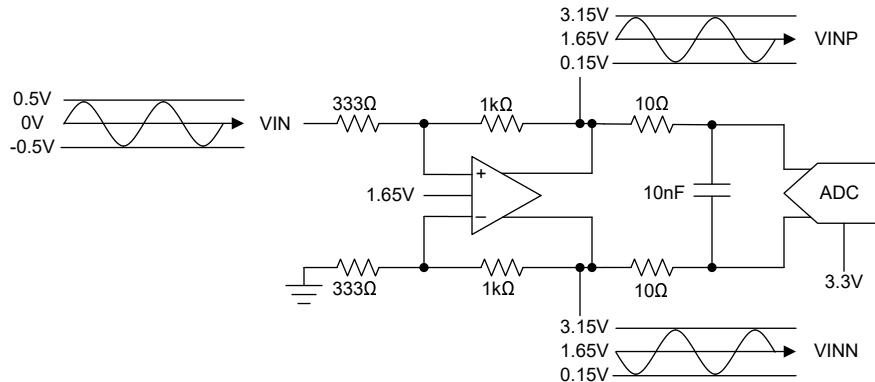
Use [Equation 3](#) to calculate  $R_{PU}$ :

$$R_{PU} = \frac{V_P - V_{CC}}{(V_{IN} - V_P) \frac{1}{R_G} + (V_{OUT} - V_P) \frac{1}{R_F}} \quad (3)$$

## 8.2 Typical Application

### 8.2.1 Typical Application

Single-to-differential conversion is a typical use-case for fully differential amplifiers (FDAs) as a result of the FDA output balance, output common-mode servo, and ADC output drive capabilities. Many higher-precision and higher-speed ADCs are moving towards differential inputs to improve common-mode noise immunity and to improve dynamic range. [Figure 8-4](#) shows how the FDA architecture allows easy conversion by simply connecting the signal source to one input and grounding the other input.



**Figure 8-4. THS4535 Single-to-Differential Conversion**

#### 8.2.1.1 Design Requirements

**Table 8-2. Design Parameters**

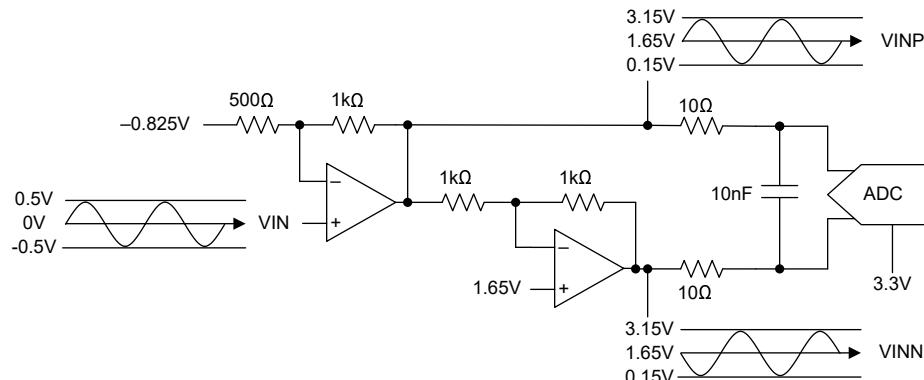
DESIGN PARAMETERS	VALUE
Input voltage	$1V_{PP}$
ADC supply voltage	3.3V
ADC input differential voltage	Balanced $6V_{PP}$
ADC input common-mode voltage	1.65V

#### 8.2.1.2 Detailed Design Procedure

The configuration shown in [Figure 8-4](#) creates a differential gain of 3, while maintaining a balanced output at the middle of the ADC range. The differential gain ( $A_{V\_DIFF}$ ) is set by the ratio of the input resistors,  $R_{IN} = 333\Omega$ , and the feedback resistors,  $R_{FB} = 1k\Omega$ , for a total of  $3V/V$ . The output common-mode is shifted to whatever voltage is specified on the  $V_{OUTCM}$  pin, which is  $\frac{1}{2}$  the ADC reference (1.65V for this example). The inherent architecture of the FDA makes two signals that are  $180^\circ$  out of phase with a maximum and minimum range of 0.15V to 3.15V. The total range of the ADC is not used in this example to provide headroom for the ADC or output range of the FDA if running on a 3.3V supply, but an alternative gain can be used to get an exact peak-to-peak voltage to match the ADC, if desired.

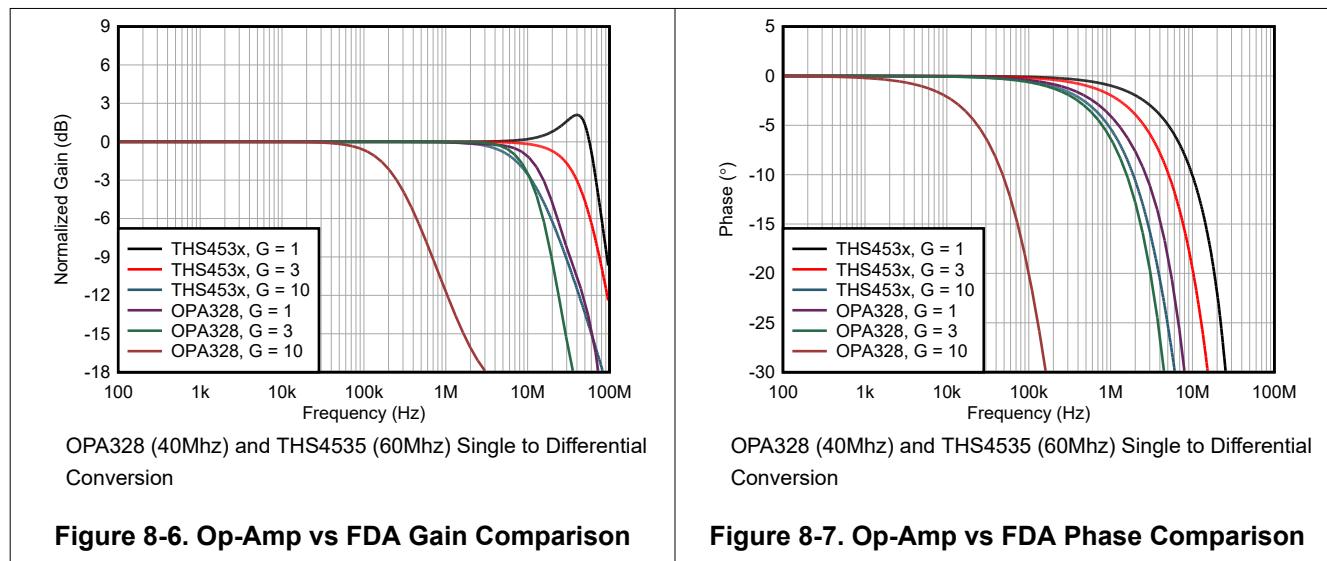
An alternative design to the FDA is a dual amplifier used in a two-op-amp instrumentation amplifier configuration. This design uses two amplifiers: one amplifier in a noninverting configuration that gains up the input signal, and one amplifier in an inverting configuration that inverts the output of the first amplifier. [Figure 8-5](#) shows there are some sizable downsides to this approach. First, the output common-mode voltage depends on the input common-mode voltage because the noninverting amplifier's output common-mode is dependent on the input common-mode voltage. This design shortcoming can be remedied by changing the dc bias of the gain resistor for the noninverting amplifier, as shown in [Figure 8-5](#) with -0.875V, but an additional bias voltage is required. Failure to shift the output common-mode voltage correctly can result in signal loss due to output clipping on the noninverting amplifier when the input voltage is close to the negative rail. Second, there is a phase imbalance between the noninverting amplifier and the inverting amplifiers in this circuit. As more gain is required of this circuit, the noninverting amplifier gets slower as the gain increases while the inverting amplifier gain stays the

same. Such gain and phase imbalances potentially manifest as distortion errors, limit signal bandwidth, and are often exacerbated with loading.



**Figure 8-5. Dual Amplifier Single-to-Dual Conversion**

#### 8.2.1.3 Application Curves



**Figure 8-6. Op-Amp vs FDA Gain Comparison**

**Figure 8-7. Op-Amp vs FDA Phase Comparison**

### 8.3 Power Supply Recommendations

The THS4535 is designed to operate on power supplies ranging from  $\pm 1.35V$  to  $\pm 2.75V$  (single-ended supplies of 2.7V to 5.5V). Use a power-supply accuracy of 5% or better. When operated on a board with high-speed digital signals, provide isolation between digital signal noise and the analog input pins. The THS4535 is connected to power supplies through the VS+ and VS- pins. Decouple each supply pin to ground as close as possible to the device with a low-inductance, surface-mount ceramic capacitor of approximately 10nF. When vias are used to connect the bypass capacitors to a ground plane, configure the vias for minimal parasitic inductance. One method of reducing via inductance is to use multiple vias. For broadband systems, two capacitors per supply pin are advised.

To avoid undesirable signal transients, do not power on the THS4535 with large input signals present. Careful planning of system power on sequencing is especially important to avoid damage to ADC inputs when an ADC is used in the application.

## 8.4 Layout

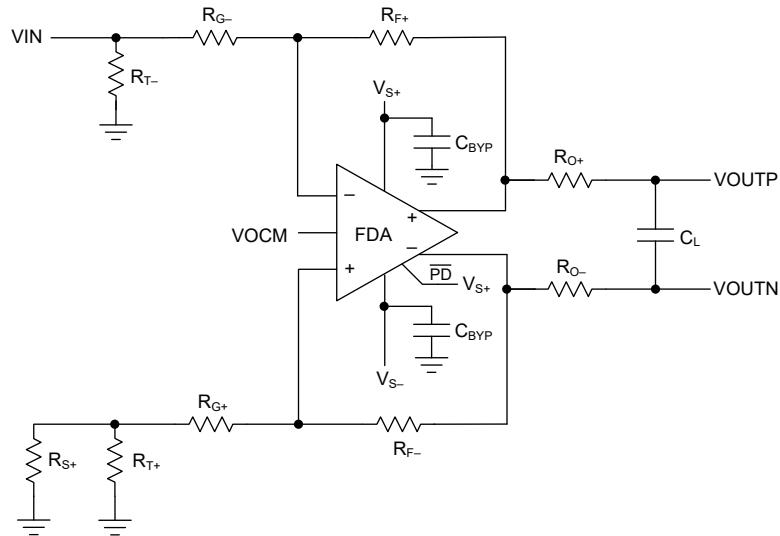
### 8.4.1 Layout Guidelines

#### 8.4.1.1 Board Layout Recommendations

Similar to all high-speed devices, best system performance is achieved with close attention to board layout. The *DEM-FDA-DGK-EVM* user's guide provides a good example of high-frequency layout techniques as a reference. This EVM includes numerous extra elements and features for characterization purposes that do not apply to some applications. General high-speed signal path layout suggestions include:

- Continuous ground planes are preferred for signal routing with matched impedance traces for longer runs; however, both ground and power planes must be opened up around the capacitive sensitive input and output device pins. When the signal goes to a resistor, parasitic capacitance becomes more of a band-limiting issue and less of a stability issue.
- Good high-frequency decoupling capacitors ( $0.1\mu\text{F}$ ) are required to a ground plane at the device power pins. Additional higher-value capacitors ( $2.2\mu\text{F}$ ) are also required but can be placed further from the device power pins and shared among devices. For best high-frequency decoupling, consider X2Y supply decoupling capacitors that offer a much higher self-resonance frequency over standard capacitors.
- Differential signal routing over any appreciable distance must use microstrip layout techniques with matched impedance traces.
- The input summing junctions are very sensitive to parasitic capacitance. Any  $R_G$  elements must connect into the summing junction with minimal trace length to the device pin side of the resistor. The other side of the  $R_G$  elements can have more trace length if needed to the source or to GND.

#### 8.4.2 Layout Examples



**Figure 8-8. Representative Schematic for the Layout Recommendations**

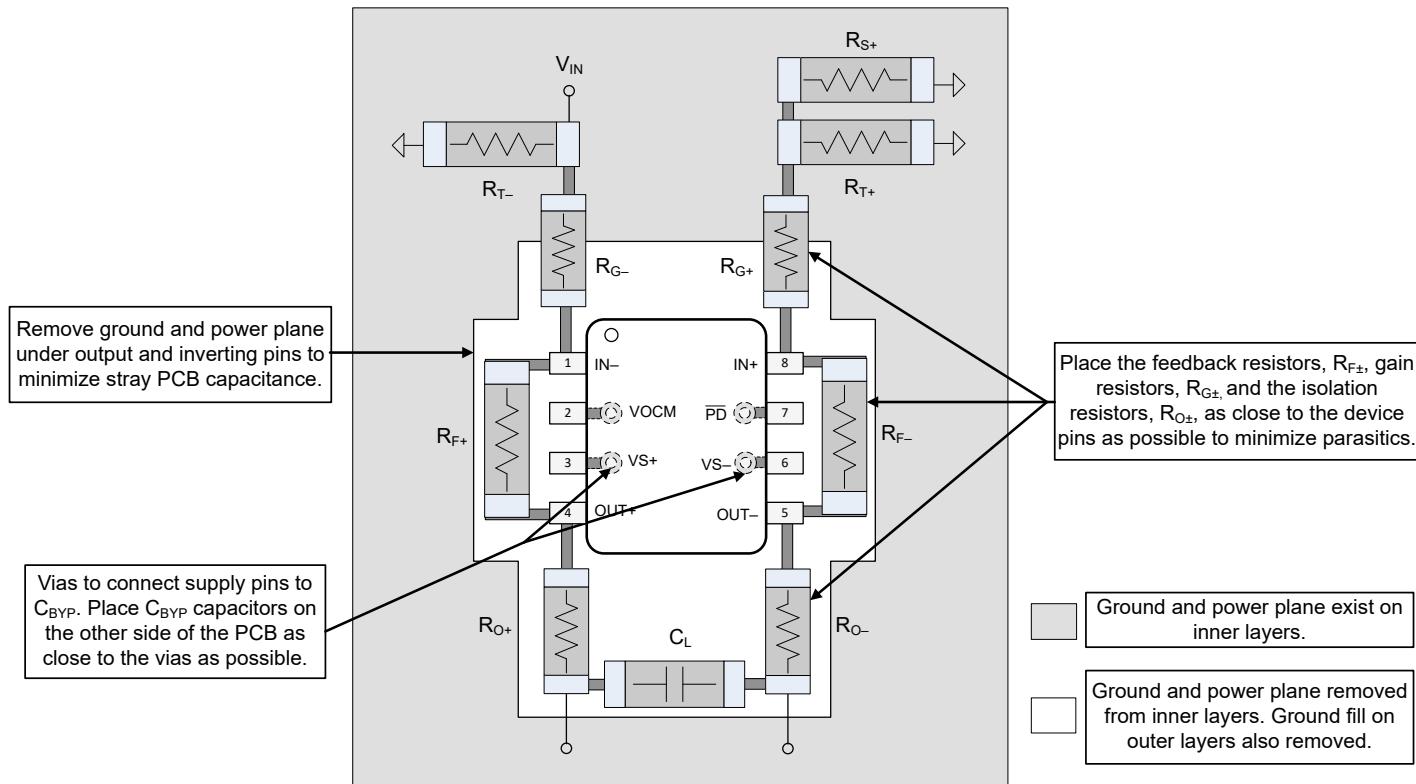


Figure 8-9. Layout Recommendations (DGK Package)

## 9 Device and Documentation Support

### 9.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](http://ti.com). Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 9.2 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

### 9.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

### 9.4 Electrostatic Discharge Caution

 This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 9.5 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

## 10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision * (June 2025) to Revision A (December 2025)	Page
• Updated data sheet status from <i>Advanced Information</i> to <i>Production Data</i> .....	<a href="#">1</a>

DATE	REVISION	NOTES
June 2025	*	Initial Release

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
THS4535DGKR	Active	Production	VSSOP (DGK)   8	2500   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	4535
THS4535RUNR	Active	Production	QFN (RUN)   10	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	4535

<sup>(1)</sup> **Status:** For more details on status, see our [product life cycle](#).

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

<sup>(4)</sup> **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

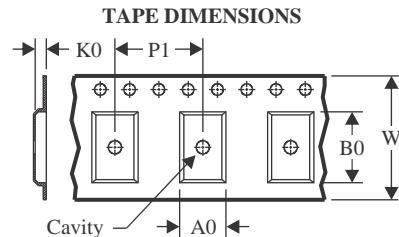
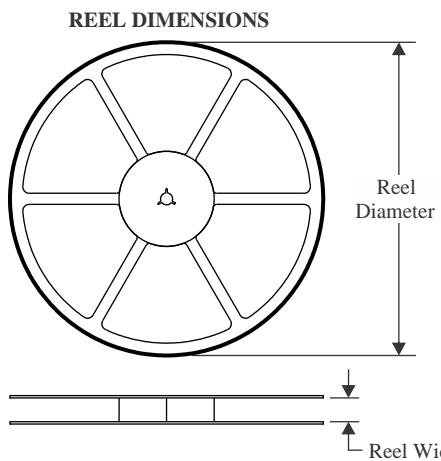
<sup>(5)</sup> **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

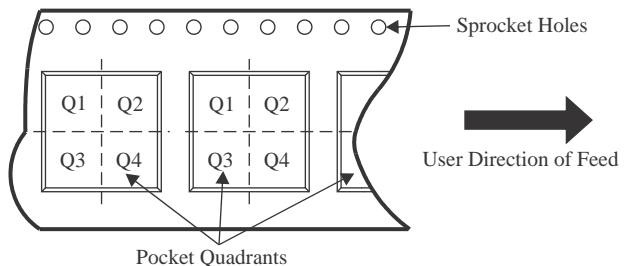
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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**TAPE AND REEL INFORMATION**


A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
THS4535DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
THS4535RUNR	QFN	RUN	10	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
THS4535DGKR	VSSOP	DGK	8	2500	353.0	353.0	32.0
THS4535RUNR	QFN	RUN	10	3000	210.0	185.0	35.0

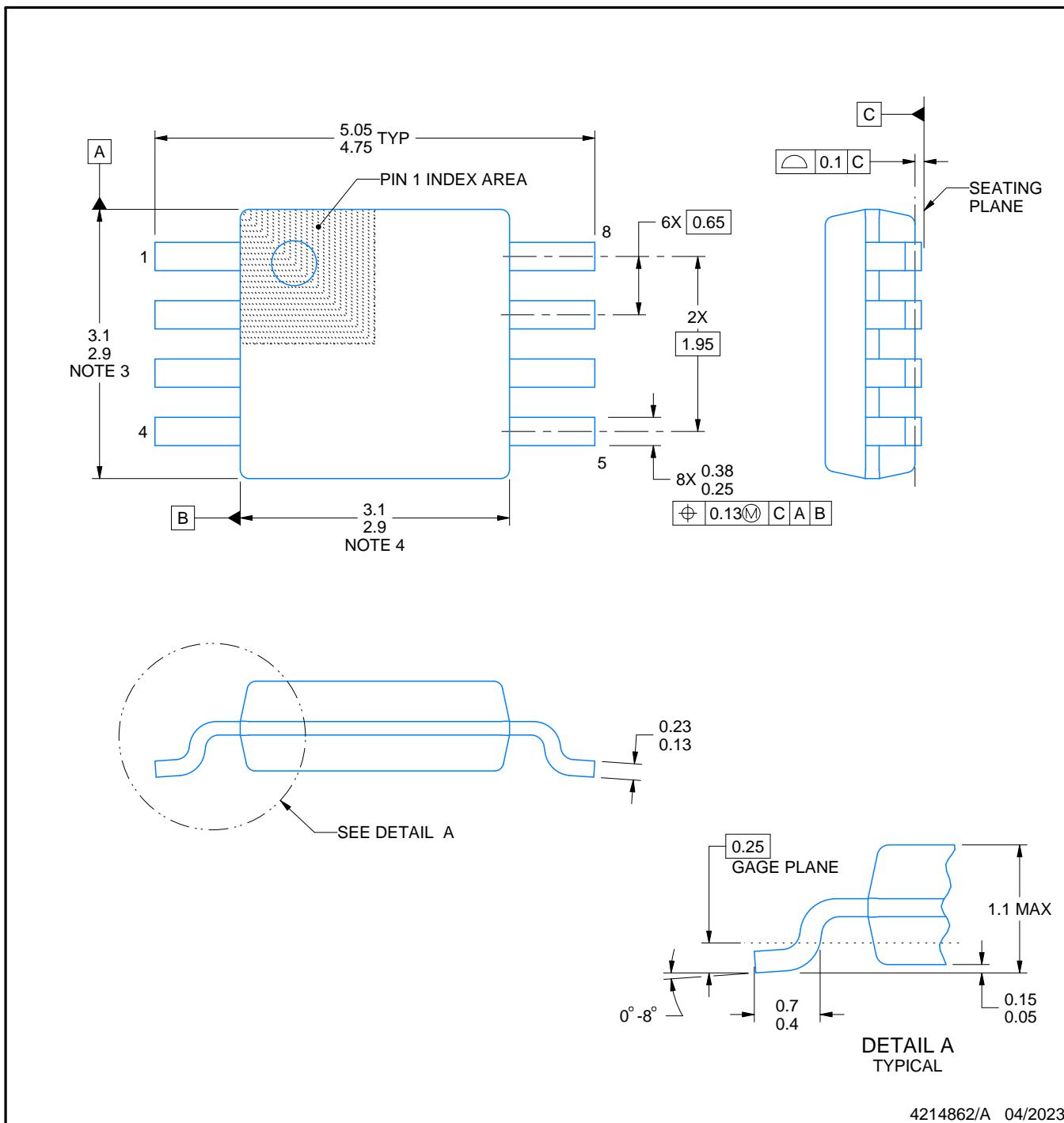
# PACKAGE OUTLINE

DGK0008A



VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



NOTES:

PowerPAD is a trademark of Texas Instruments.

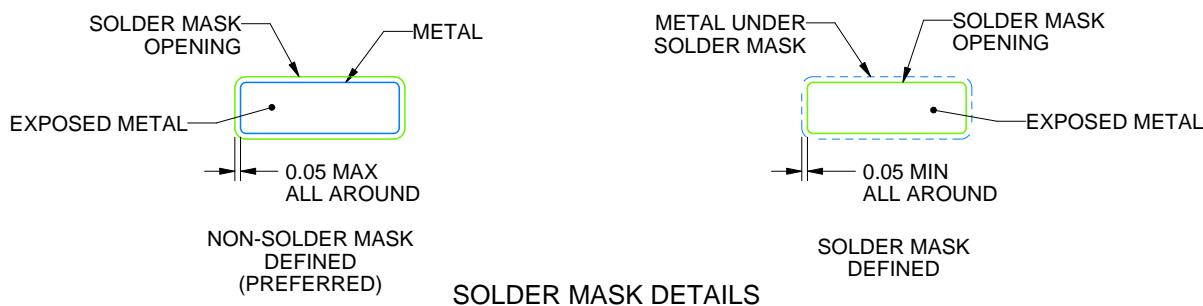
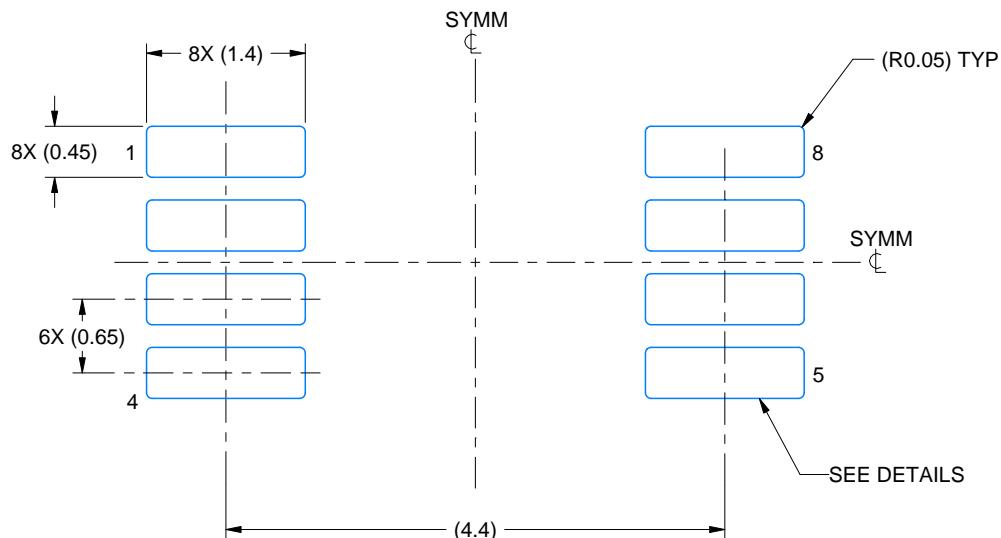
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.

# EXAMPLE BOARD LAYOUT

DGK0008A

™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



4214862/A 04/2023

NOTES: (continued)

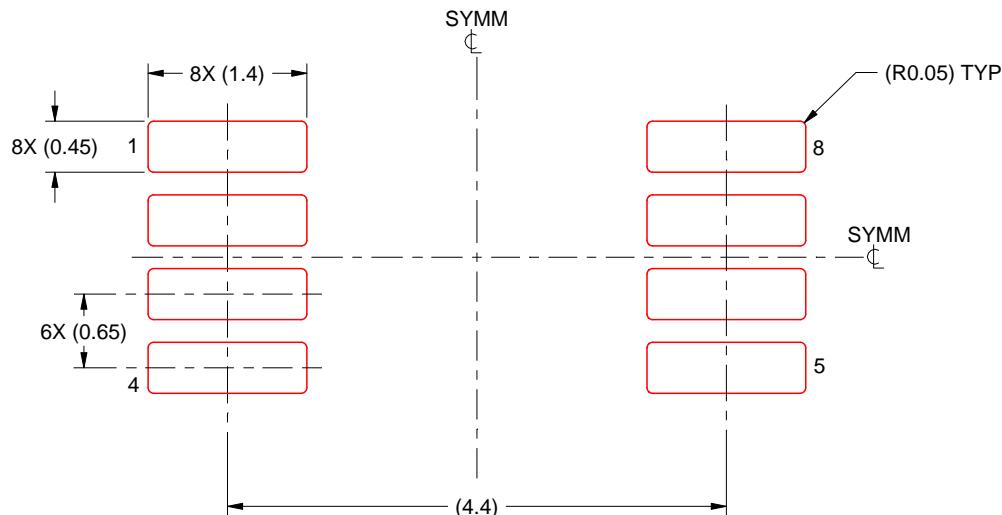
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
9. Size of metal pad may vary due to creepage requirement.

# EXAMPLE STENCIL DESIGN

DGK0008A

TM VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
SCALE: 15X

4214862/A 04/2023

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

# GENERIC PACKAGE VIEW

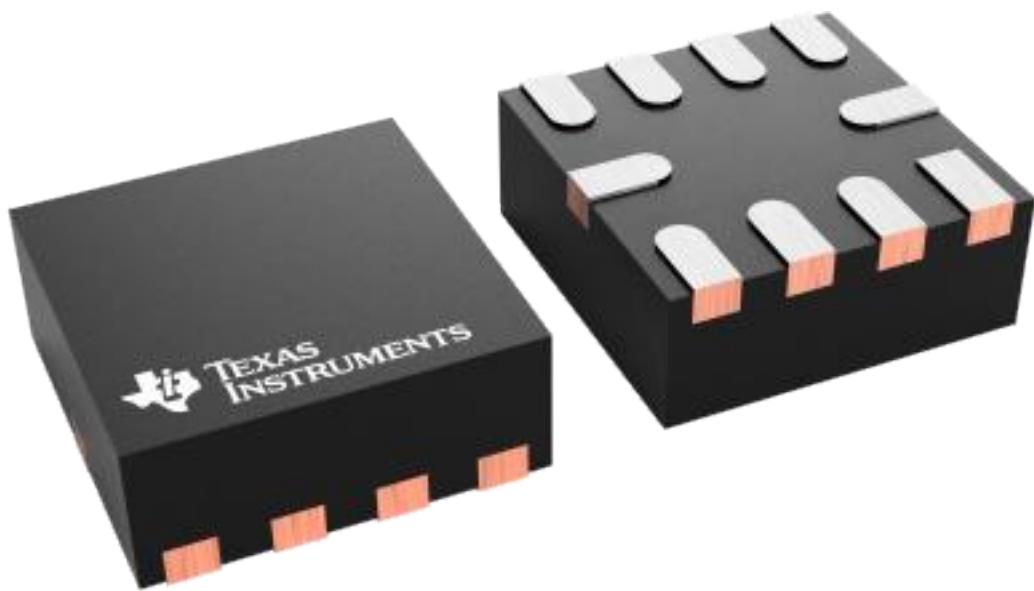
## RUN 10

## WQFN - 0.8 mm max height

2 X 2, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

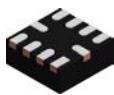
This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



4228249/A

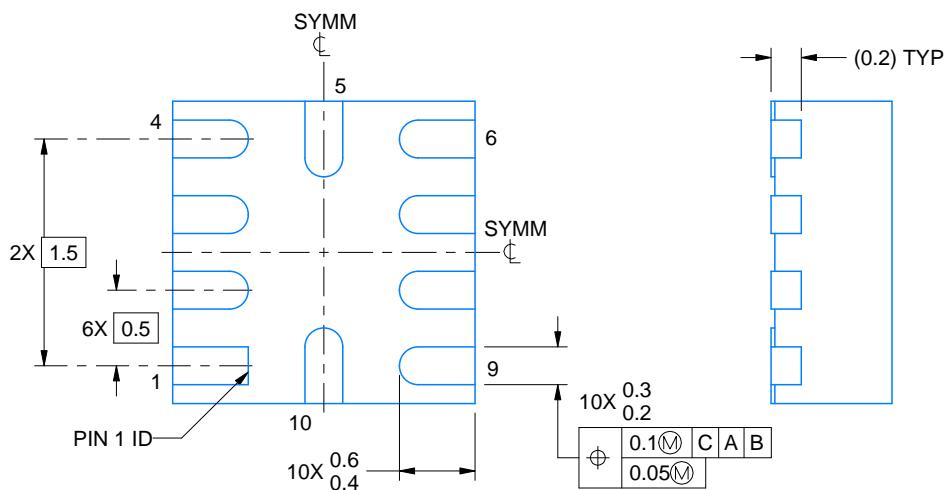
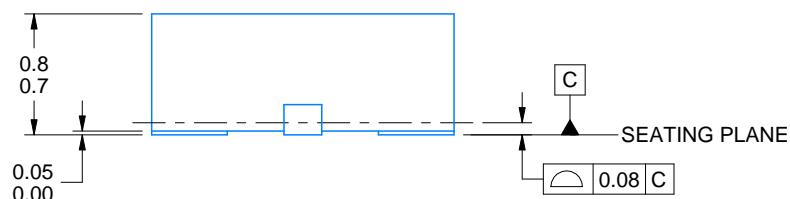
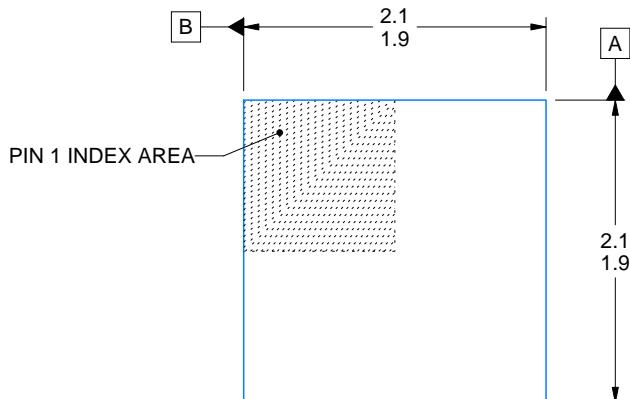
# PACKAGE OUTLINE

RUN0010A



WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



4220470/A 05/2020

## NOTES:

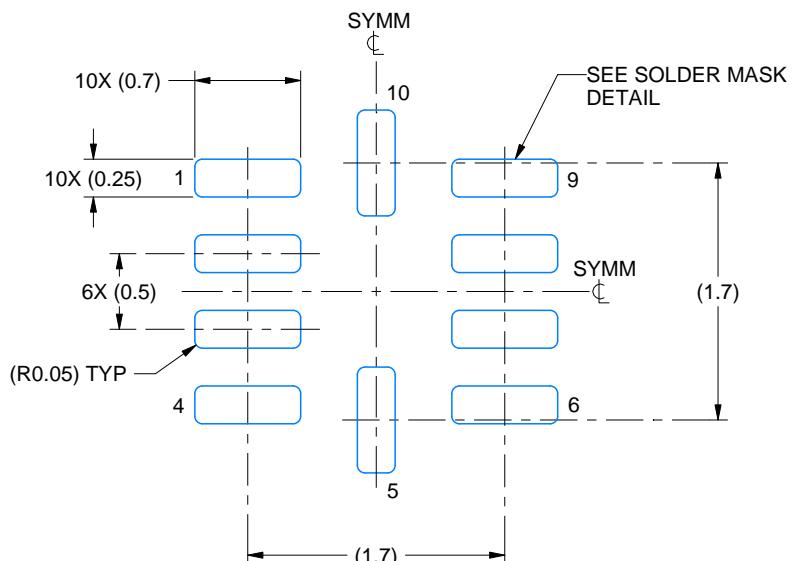
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

# EXAMPLE BOARD LAYOUT

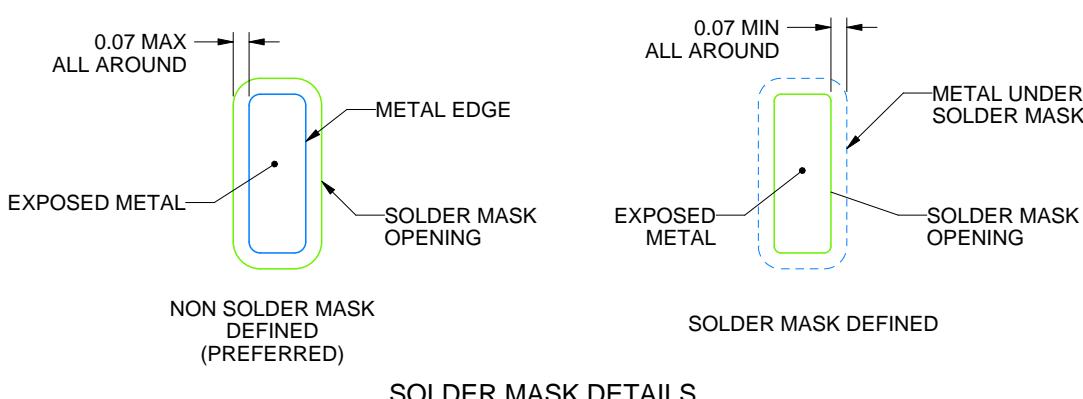
RUN0010A

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 20X



4220470/A 05/2020

NOTES: (continued)

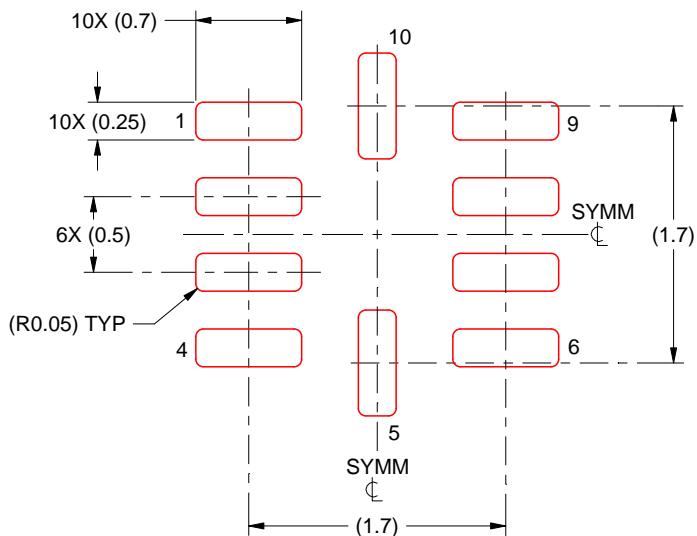
3. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/slua271](http://www.ti.com/lit/slua271)).

# EXAMPLE STENCIL DESIGN

**RUN0010A**

**WQFN - 0.8 mm max height**

PLASTIC QUAD FLATPACK - NO LEAD



**SOLDER PASTE EXAMPLE**  
BASED ON 0.125 MM THICK STENCIL  
SCALE: 20X

4220470/A 05/2020

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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